

TOSHIBA TRANSISTOR SILICON-GERMANIUM NPN EPITAXIAL PLANER TYPE

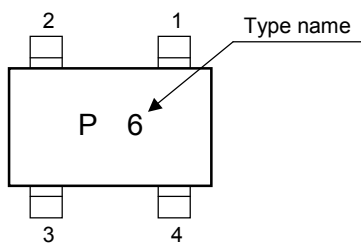
# MT4S100U

UHF LOW NOISE AMPLIFIER APPLICATION

## FEATURES

- Low Noise Figure :NF=0.72dB (@f=2GHz)
- High Gain:|S<sub>21e</sub>|<sup>2</sup>=16.0dB (@f=2GHz)

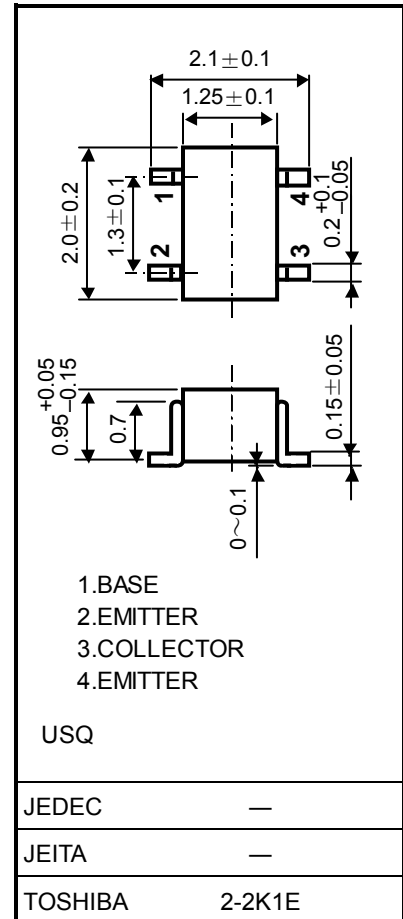
## Marking



## Maximum Ratings (Ta = 25°C)

| Characteristics             | Symbol           | Rating  | Unit |
|-----------------------------|------------------|---------|------|
| Collector-Base voltage      | V <sub>CB0</sub> | 6       | V    |
| Collector-Emitter voltage   | V <sub>CEO</sub> | 3       | V    |
| Emitter-Base voltage        | V <sub>EBO</sub> | 1.2     | V    |
| Collector-Current           | I <sub>C</sub>   | 15      | mA   |
| Base-Current                | I <sub>B</sub>   | 7       | mA   |
| Collector Power dissipation | P <sub>C</sub>   | 45      | mW   |
| Junction temperature        | T <sub>j</sub>   | 150     | °C   |
| Storage temperature Range   | T <sub>stg</sub> | -55~150 | °C   |

Unit: mm



Weight: 0.006 g (typ.)

**Microwave Characteristics (Ta = 25°C)**

| Characteristics      | Symbol                          | Test Condition                                    | Min  | Typ. | Max | Unit |
|----------------------|---------------------------------|---------------------------------------------------|------|------|-----|------|
| Transition Frequency | f <sub>T</sub>                  | V <sub>CE</sub> =2V, I <sub>C</sub> =10mA, f=2GHz | 18   | 22   | -   | GHz  |
| Insertion Gain       | S <sub>21e</sub>   <sup>2</sup> | V <sub>CE</sub> =2V, I <sub>C</sub> =10mA, f=2GHz | 13.5 | 16   | -   | dB   |
| Noise Figure         | NF                              | V <sub>CE</sub> =2V, I <sub>C</sub> =5mA, f=2GHz  | -    | 0.72 | 1.0 | dB   |

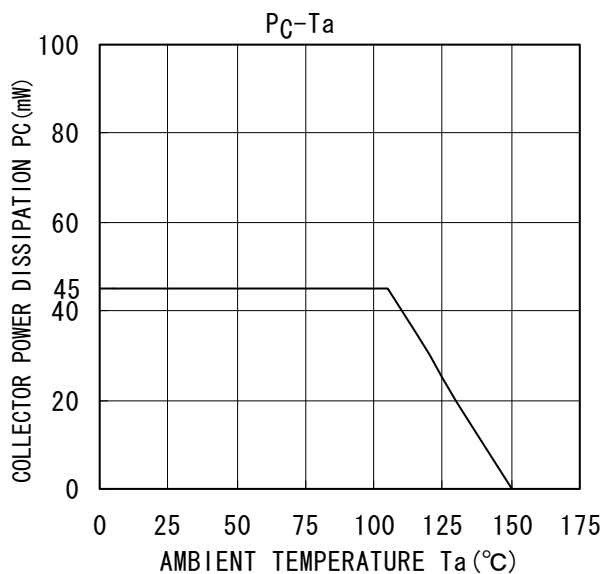
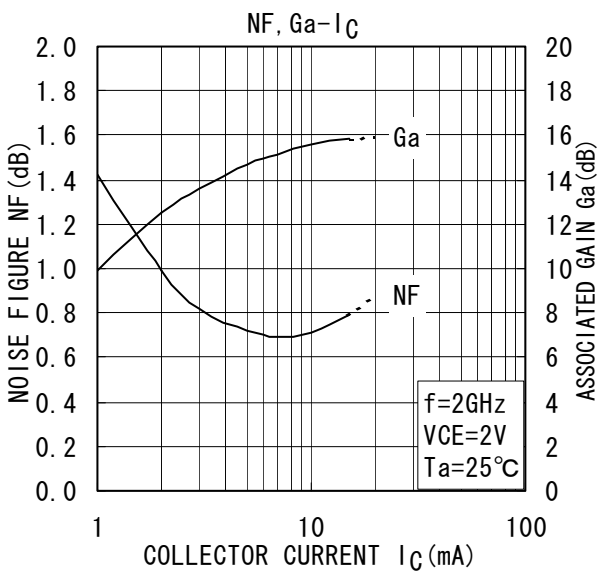
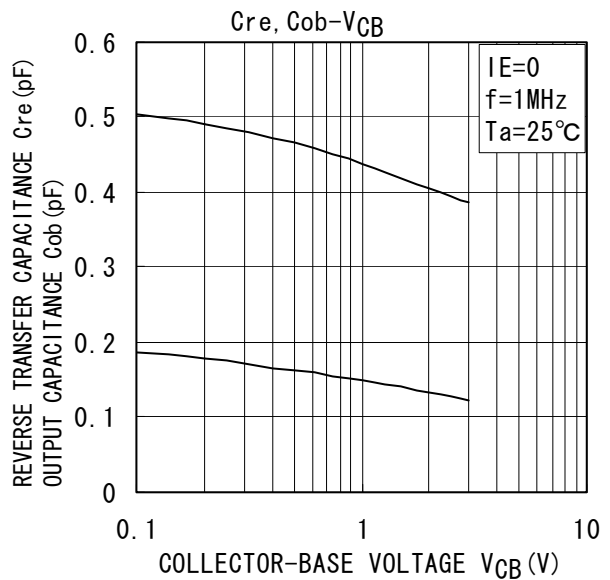
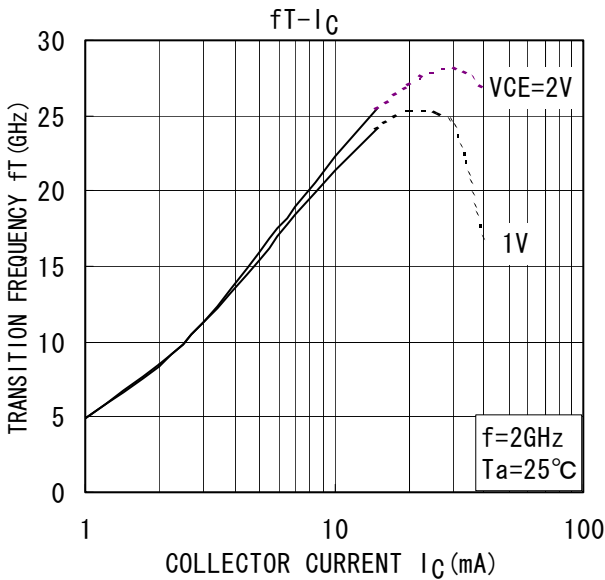
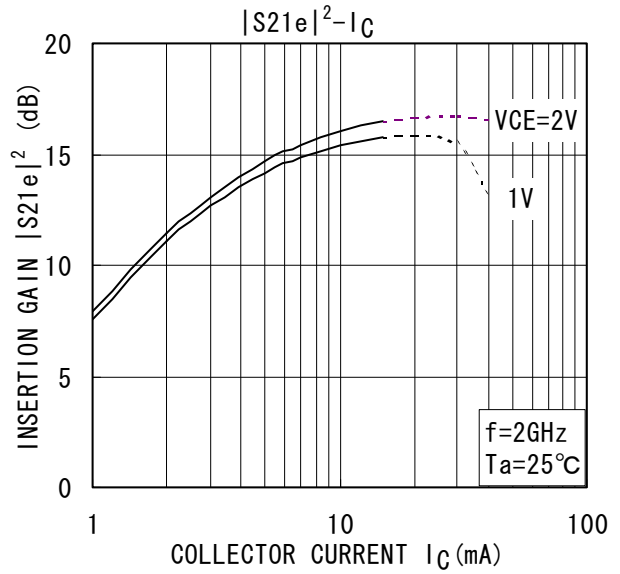
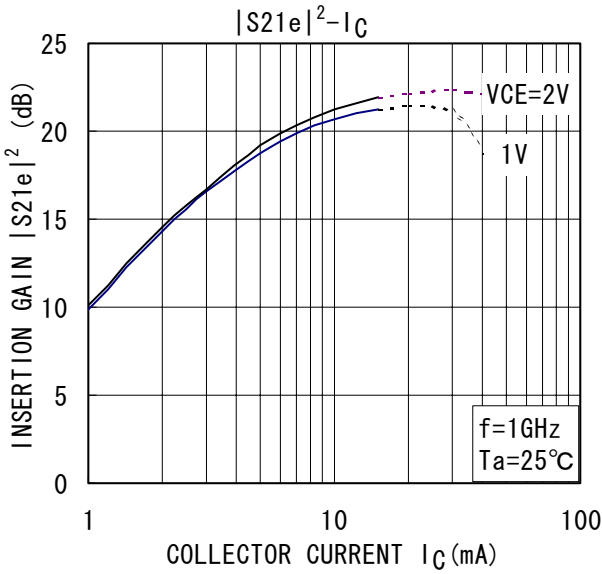
**Electrical Characteristics (Ta = 25°C)**

| Characteristics                | Symbol           | Test Condition                                          | Min | Typ. | Max | Unit |
|--------------------------------|------------------|---------------------------------------------------------|-----|------|-----|------|
| Collector Cut-off Current      | I <sub>CB0</sub> | V <sub>CB</sub> =6V, I <sub>E</sub> =0                  | -   | -    | 1   | μA   |
| Emitter Cut-off Current        | I <sub>EB0</sub> | V <sub>EB</sub> =1V, I <sub>C</sub> =0                  | -   | -    | 1   | μA   |
| DC Current Gain                | hFE              | V <sub>CE</sub> =2V, I <sub>C</sub> =10mA               | 200 | -    | 400 | -    |
| Output Capacitance             | C <sub>ob</sub>  | V <sub>CB</sub> =2V, I <sub>E</sub> =0, f=1MHz          | -   | 0.41 | 0.6 | pF   |
| Reverse Transistor Capacitance | C <sub>re</sub>  | V <sub>CB</sub> =2V, I <sub>E</sub> =0, f=1MHz (Note 1) | -   | 0.14 | 0.2 | pF   |

**Note 1:** C<sub>re</sub> is measured by 3 terminal method with capacitance bridge.

**Caution:** This device is sensitive to electrostatic discharge.

Please make enough tool and equipment earthed when you handle.



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